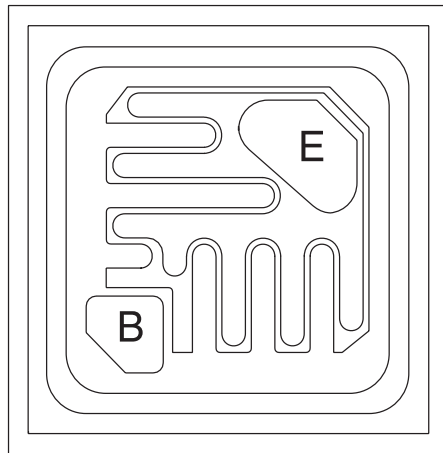


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	4.0 x 4.0 MILS
Emitter Bonding Pad Area	4.7 x 4.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY

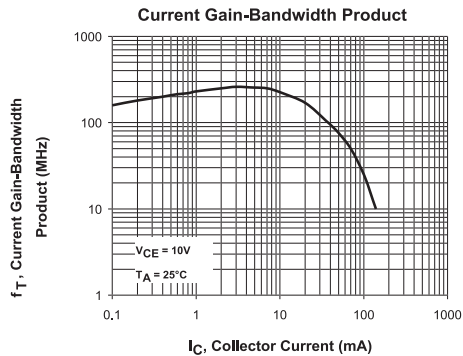
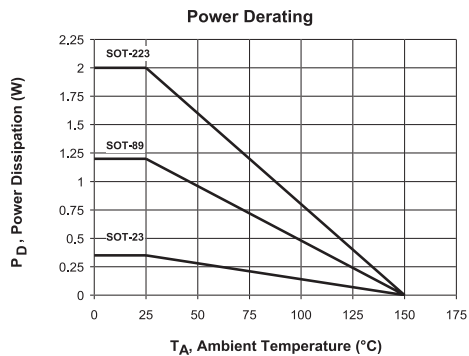
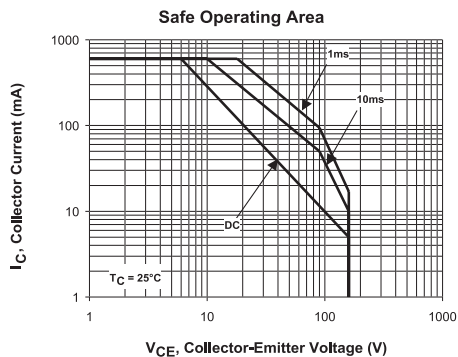
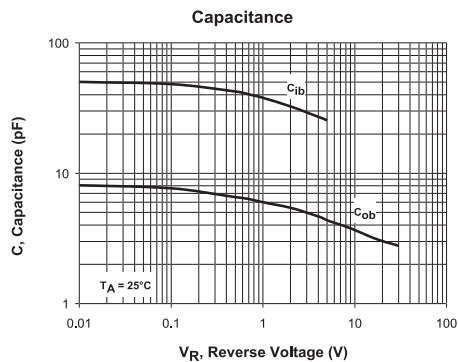
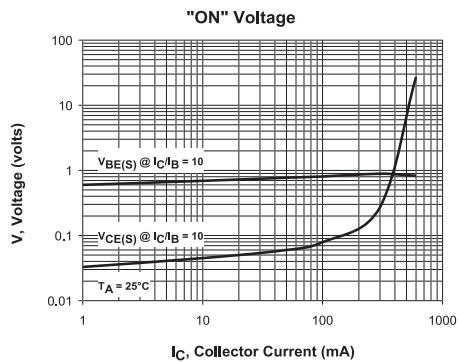
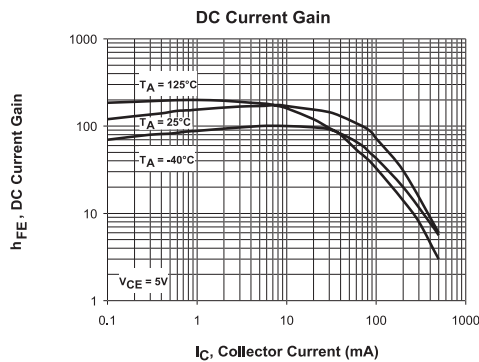
BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

29,250

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R0 (22-March 2005)



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